HEF4049B

Hex inverting buffers

Rev. 04 — 4 July 2008

Product data sheet

1. General description

The HEF4049B provides six inverting buffers with high current output capability suitable for driving TTL or high capacitive loads. Since input voltages in excess of the buffers' supply voltage are permitted, the buffers may also be used to convert logic levels of up to 15 V to standard TTL levels. Their guaranteed fan-out into common bipolar logic elements is shown in Table 3.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input. The HEF4049B is suitable for use over the industrial (–40 °C to +85 °C) and automotive (–40 °C to +125 °C) temperature ranges.

2. Features

- Accepts input voltages in excess of the supply voltage
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Operates across the automotive temperature range -40 °C to +125 °C
- Complies with JEDEC standard JESD 13-B
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V

3. Applications

- LOCMOS (Local Oxidation CMOS) to DTL/TTL converter
- HIGH sink current for driving two TTL loads
- HIGH-to-LOW level logic conversion

4. Ordering information

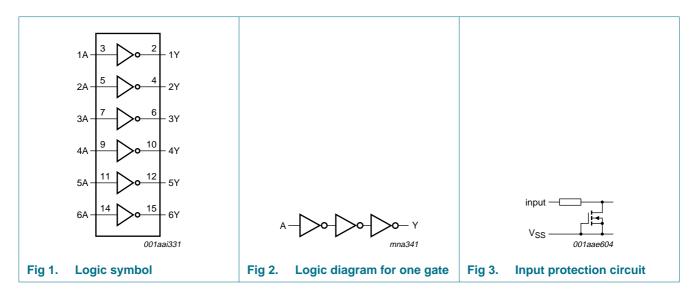
Table 1. Ordering information

All types operate from $-40 \,^{\circ}\text{C}$ to $+125 \,^{\circ}\text{C}$.

Type number	Package							
	Name	Description	Version					
HEF4049BP	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4					
HEF4049BT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1					

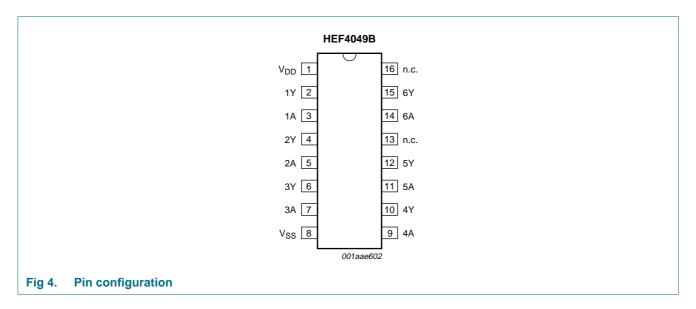


5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
V_{DD}	1	supply voltage
1Y to 6Y	2, 4, 6, 10, 12, 15	output

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Table 2. Pin description ... continued

Symbol	Pin	Description
1A to 6A	3, 5, 7, 9, 11, 14	input
V _{SS}	8	ground supply voltage
n.c.	13, 16	not connected

7. Functional description

Table 3. Guaranteed fan-out

Driven element	Guaranteed fan-out
Standard TTL	2
74 LS	9
74 L	16

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). T_{amb} = -40 °C to +125 °C.

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
V_{I}	input voltage	any input	-0.5	$V_{DD} + 0.5$	V
I _{I/O}	input/output current		-	±10	mA
T_{stg}	storage temperature		-65	+150	°C
T_{amb}	ambient temperature		-40	+125	°C
P _{tot}	total power dissipation	DIP16 package	<u>[1]</u> _	750	mW
		SO16 package	[2] _	500	mW
Р	power dissipation	per output	-	100	mW

^[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	supply voltage		3	-	15	V
VI	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	ns/V
		$V_{DD} = 10 \text{ V}$	-	-	0.5	ns/V
		V _{DD} = 15 V	-	-	0.08	ns/V

^[2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

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10. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0 \ V$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	s V _{DD}	T _{amb} =	-40 °C	T _{amb} =	: 25 °C	T _{amb} =	85 °C	T _{amb} =	125 °C	Unit	
				Min	Max	Min	Max	Min	Max	Min	Max		
V_{IH}	HIGH-level	$ I_{O} < 1 \mu A$	5 V	3.5	-	3.5	-	3.5	-	3.5	-	V	
	input voltage		10 V	7.0	-	7.0	-	7.0	-	7.0	-	V	
			15 V	11.0	-	11.0	-	11.0	-	11.0	-	V	
V_{IL}	LOW-level	$ I_{O} < 1 \mu A$	5 V	-	1.5	-	1.5	-	1.5	-	1.5	V	
	input voltage		10 V	-	3.0	-	3.0	-	3.0	-	3.0	V	
			15 V	-	4.0	-	4.0	-	4.0	-	4.0	V	
V_{OH}	HIGH-level	$ I_{O} < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V	
	output voltage		10 V	9.95	-	9.95	-	9.95	-	9.95	-	V	
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V	
V_{OL}	LOW-level	$ I_O < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V	
	output voltage		10 V	-	0.05	-	0.05	-	0.05	-	0.05	V	
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V	
I _{OH}	HIGH-level		$V_0 = 2.5 \ V$	5 V	-1.7	-	-1.4	-	-1.1	-	-1.1	-	mΑ
	output current	$V_{O} = 4.6 \text{ V}$	5 V	-0.64	-	-0.5	-	-0.36	-	-0.36	-	mΑ	
		$V_0 = 9.5 \ V$	10 V	-1.6	-	-1.3	-	-0.9	-	-0.9	-	mΑ	
		$V_0 = 13.5 \text{ V}$	15 V	-4.2	-	-3.4	-	-2.4	-	-2.4	-	mΑ	
I_{OL}	LOW-level	$V_O = 0.4 V$	4.75 V	3.6	-	2.9	-	2.3	-	1.9	-	mΑ	
	output current	$V_{O} = 0.5 \ V$	10 V	12.5	-	10.0	-	8.0	-	6.7	-	mΑ	
		$V_0 = 1.5 \text{ V}$	15 V	25.0	-	20.0	-	16.0	-	13.0	-	mΑ	
l _l	input leakage current	$V_{DD} = 15 \text{ V}$	15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μΑ	
I_{DD}	supply current	$I_O = 0 A$	5 V	-	1.0	-	1.0	-	30	-	30	μΑ	
			10 V	-	2.0	-	2.0	-	60	-	60	μΑ	
			15 V	-	4.0	-	4.0	-	120	-	120	μΑ	
Cı	input capacitance			-	-	-	7.5	-	-	-	-	pF	

11. Dynamic characteristics

Table 7. Dynamic characteristics

 $V_{SS} = 0$ V; $C_L = 50$ pF; $t_f = t_f \le 20$ ns; $T_{amb} = 25$ °C; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Тур	Max	Unit
TIL	HIGH to LOW	nA to nY; see <u>Figure 5</u>	5 V	11 26 ns + (0.18 ns/pF)C _L	-	35	70	ns
	propagation delay		10 V	11 ns + (0.08 ns/pF)C _L	-	15	30	ns
			15 V	9 ns + $(0.05 \text{ ns/pF})C_L$	-	12	25	ns
t _{PLH}	LOW to HIGH propagation delay	see Figure 5	5 V	11 23 ns + (0.55 ns/pF)C _L	-	50	100	ns
			10 V	14 ns + (0.23 ns/pF)C _L	-	25	50	ns
			15 V	12 ns + (0.16 ns/pF)C _L	-	20	40	ns

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 Table 7.
 Dynamic characteristics ...continued

 $V_{SS} = 0 \text{ V; } C_L = 50 \text{ pF; } t_f = t_f \le 20 \text{ ns; } T_{amb} = 25 \,^{\circ}\text{C; unless otherwise specified.}$

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Тур	Max	Unit
TITLE	HIGH to LOW output	see Figure 5	5 V	11 3 ns + $(0.35 \text{ ns/pF})C_L$	-	20	40	ns
	transition time		10 V	3 ns + $(0.14 \text{ ns/pF})C_L$	-	10	20	ns
			15 V	$2 \text{ ns + } (0.09 \text{ ns/pF})C_L$	-	7	14	ns
t _{TLH}	LOW to HIGH output transition time	10 \	5 V	10 ns + (1.00 ns/pF)C _L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns

^[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

Table 8. Dynamic power dissipation P_D

 P_D can be calculated from the formulas shown. $V_{SS} = 0$ V; $t_r = t_f \le 20$ ns; $T_{amb} = 25$ °C.

Symbol	Parameter	V_{DD}	Typical formula for P _D (μW)	where:
P_D	dynamic power	5 V	$P_D = 2500 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	f _i = input frequency in MHz;
	dissipation	10 V	$P_D = 11000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	fo = output frequency in MHz;
		15 V	$P_D = 35000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	C _L = output load capacitance in pF;
				V_{DD} = supply voltage in V;
				$\Sigma(C_L \times f_o)$ = sum of the outputs.

12. Waveforms

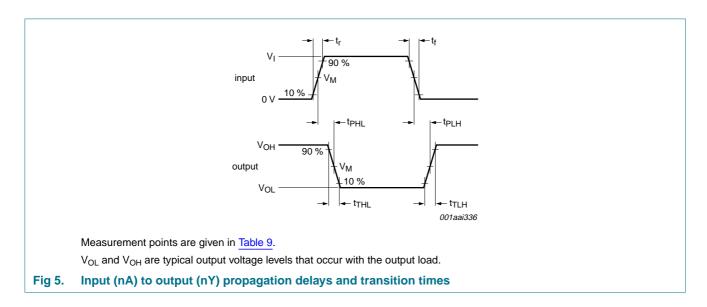
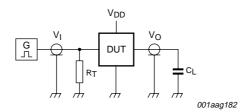


Table 9. Measurement points

Input	Output	
V _M	V _I	V _M
0.5V _{DD}	0 V to V _{DD}	0.5V _{DD}

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Test data is given in Table 10.

Definitions for test circuit:

 C_L = Load capacitance including jig and probe capacitance.

 $R_{T} = \mbox{Termination} \ \mbox{resistance} \ \mbox{should} \ \mbox{be} \ \mbox{equal} \ \mbox{to} \ \mbox{output} \ \mbox{impedance} \ \mbox{Z}_{0} \ \mbox{of} \ \mbox{the} \ \mbox{pulse} \ \mbox{generator}.$

Fig 6. Load circuitry for switching times

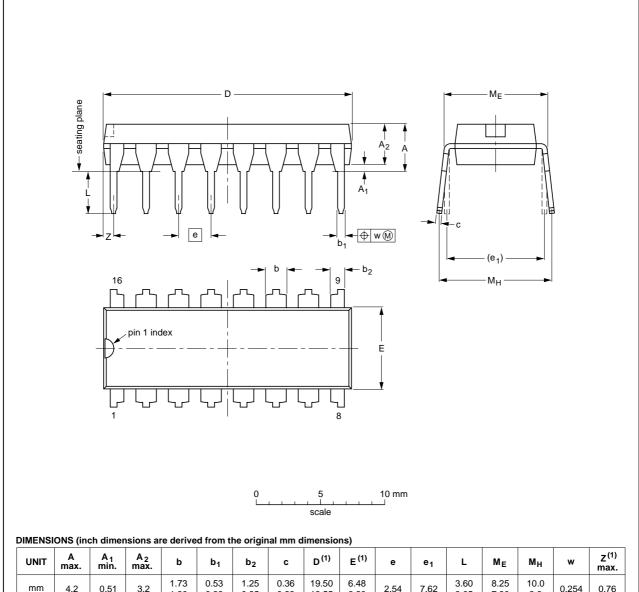
Table 10. Test data

Supply voltage	Input	Load		
	VI	V _M	t _r , t _f	CL
5 V to 15 V	V_{DD}	0.5V _I	≤ 20 ns	50 pF

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note

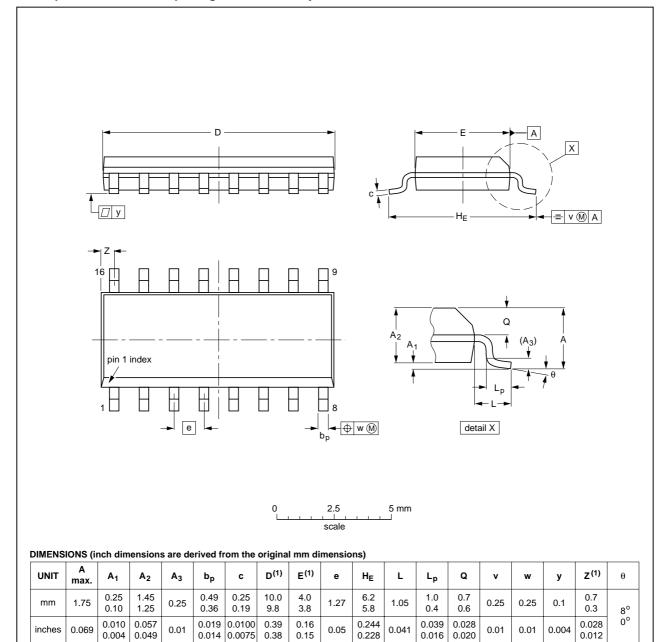
1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT38-4						95-01-14 03-02-13

Package outline SOT38-4 (DIP16) Fig 7.

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				99-12-27 03-02-19	

Fig 8. Package outline SOT109-1 (SO16)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
DUT	Device Under Test
DTL	Diode Transistor Logic
ESD	ElectroStatic Discharge
HBM	Human Body Model
LOCMOS	Local Oxidation CMOS
MM	Machine Model
TTL	Transistor Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
HEF4049B_4	20080704	Product data sheet	-	HEF4049B_CNV_3				
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 							
	 Legal texts have been adapted to the new company name where appropriate. 							
	Pins renamed throughout.							
	 Maximum ambient temperature increased to 125 °C. 							
	 Package version SOT38-1 changed to SOT38-4 in <u>Section 4</u>, and <u>Figure 7</u>. Package SOT74 removed from <u>Section 4</u>. 							
	 Section 2 "Features" added. 							
		 <u>Section 8 "Limiting values"</u> and <u>Section 10 "Static characteristics"</u> added, taken from the HE4000B Family Specifications data sheet. 						
	Section 9 "	 Section 9 "Recommended operating conditions" added. 						
	 Section 10 "Static characteristics" IDD, IOL, IOH, and II values updated. 							
	 Section 14 	"Abbreviations" added.						
HEF4049B_CNV_3	19950101	Product specification	-	HEF4049B_CNV_2				
HEF4049B CNV 2	19950101	Product specification	_	_				

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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